Product data sheet

1. General description

Silicon Carbide Schottky diode in a SOD59A (TO-220AC) plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- · Highly stable switching performance
- High forward surge capability I_{FSM}
- · Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- · Power factor correction
- Telecom/Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED/OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	650	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 112 °C; square-wave pulse; Fig. 1; Fig. 2	-	-	10	A
Tj	junction temperature		-	-	175	°C
Static charac	teristics					
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.5	1.7	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.8	2.1	V
Dynamic cha	racteristics					,
Q _r	recovered charge	I _F = 10 A; dI _F /dt = 500 A/μs; V _R = 400 V; T _j = 25 °C; <u>Fig. 5</u>	-	15	22	nC

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	А	anode	$\frac{1}{2} \bigcirc \zeta$	001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59A)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NXPSC10650	TO-220AC	Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59A			

7. Marking

Table 4. Marking codes

Type number	Marking code
NXPSC10650	NXPSC10650

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	650	V
V_{RWM}	crest working reverse voltage		-	650	V
V_R	reverse voltage	DC	-	650	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 112 °C; square-wave pulse; Fig. 1; Fig. 2	-	10	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le 112$ °C; square-wave pulse	-	20	А
I _{FSM}	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse	-	50	Α
forward current	t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse	-	450	А	
I ² t	I ² t for fusing	sine-wave pulse; $T_{j(init)}$ = 25 °C; t_p = 10 ms	-	12.5	A²s
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-	175	°C

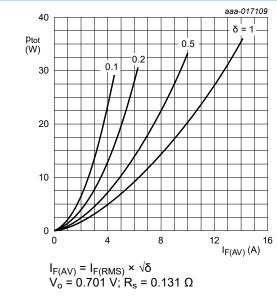


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

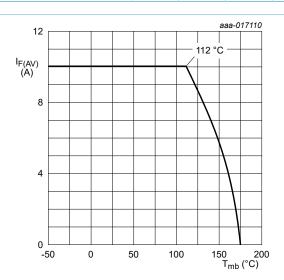


Fig. 2. Forward current as a function of mounting base temperature; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 3	-	-	1.9	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

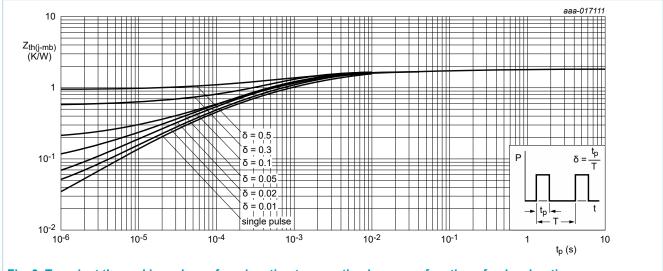


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					,
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.5	1.7	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.8	2.1	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	100	μΑ
		V _R = 600 V; T _j = 150 °C	-	-	450	μΑ
		V _R = 650 V; T _j = 25 °C	-	-	250	μΑ
		V _R = 650 V; T _j = 150 °C	-	-	800	μΑ
Dynamic ch	naracteristics					
Q _r	recovered charge	$I_F = 10 \text{ A}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $V_R = 400 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 5$	-	15	22	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	300	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	34	-	pF
		f = 1 MHz; V _R = 600 V; T _i = 25 °C	-	28	40	pF

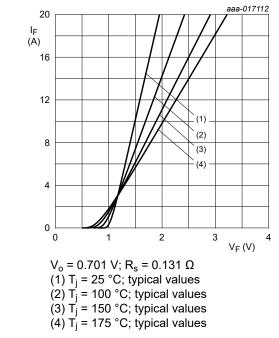


Fig. 4. Forward current as a function of forward voltage; typical values

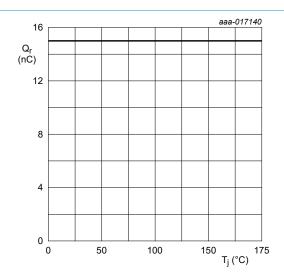
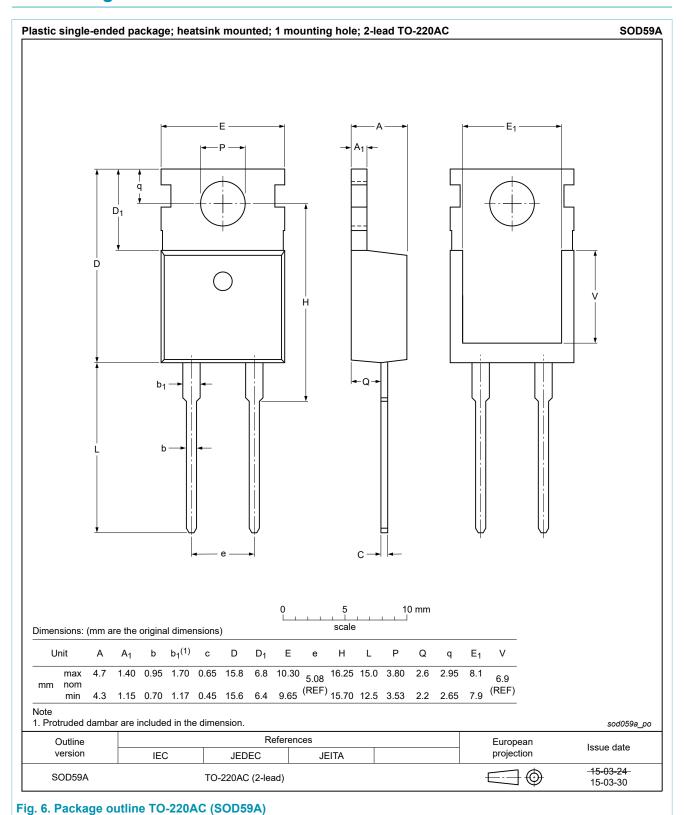


Fig. 5. Recovered charge as a function of junction temperature

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11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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